L Number	Hits	Search Text	DB	Time stamp
16	1623	<pre>(si or silicon) near2 single near2 crystal\$5 near2 (substrate or wafer) near5 insulat\$5</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:46
17	854	(si or silicon) near2 single near2 crystal\$5 near2 (substrate or wafer) near5 insulat\$5 and @py<1999	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:46
18	82	(si or silicon) near2 single near2 crystal\$5 near2 (substrate or wafer) near5 insulat\$5 and @py<1999 and 117/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:52
19	1	(tft or thin near2 film near2 transistor) same (sige or silicon near2 germanium) near4 grad\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:54
20	66	(sige or silicon near2 germanium) near4 grad\$4 same insulat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:54
21	. 11	(sige or silicon near2 germanium) near4 grad\$4 near10 insulat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:56
22	151	(sige or silicon near2 germanium) near4 grad\$4 same relax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 11:56
23	29	(sige or silicon near2 germanium) near4 grad\$4 same electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11
24	604	(sige or silicon near2 germanium) near16 ion near2 implant\$5	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11 11:58
25	65	(sige or silicon near2 germanium) near16 ion near2 implant\$5 near10 concentrat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:40
26	41	(sige or silicon near2 germanium) near16 ion near2 implant\$5 near5 (ge or germanium) near10 concentrat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:52
27	345	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:53
28	92	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:53
29	5	heterojunction near2 bipolar near2 transistor same (silicon or si) near2 substrate near5 insulat\$5 same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/11 12:55

Search History 5/11/

5/11/04 4:24:28 PM

Page 1

	A 15				
30	野公園	0	heterojunction near2 bipolar near2 transistor same (quartz) near2 substrate same (sige or silicon near2 germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11 12:55
31	o triggi special in	0	heterojunction near2 bipolar near2 transistor same (quartz) near2 substrate	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/11 12:55
32		216	heterojunction near2 bipolar near2 transistor same insulat\$4 near2 substrate	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/11 12:58
33		520	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/11 12:59
34		25	<pre>same (sige or silicon near2 germanium) near10 (anneal\$4 or heat near2 treat\$4 or</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11
35		1	laser) (thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium) near10 grad\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11 13:00
36		11	(thin near2 film near2 transistor or tft) same (sige or silicon near2 germanium) near10 combin\$6	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11 13:03
37		662	amorphous near2 (silicon or si) same amorphous near5 (sige or silicon adj germanium) same (crystal\$5 or	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11 13:04
38		72	crystalliz\$4 or recrystal\$4 or recrystalliz\$4) amorphous near2 (silicon or si) same amorphous near5 (sige or silicon adj germanium) same (crystal\$5 or crystalliz\$4 or recrystal\$4 or recrystalliz\$4) near10 (laser or heat	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/11
39		142	near2 treat\$4 or anneal\$4) (thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11
40		1	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility) same (sige or silicon near2 germanium)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11 13:17
41		142	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11 13:17
42		74	(thin near2 film near2 transistor or tft) same (low near2 carrier near2 mobility) and @py<2002	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11 13:20
43	į	33	(thin near2 film near2 transistor or tft) same (carrier near2 mobility) near10 "100" and @py<2002	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/11
1				IBM TDB	

Search History 5/11/04 4:24:28 PM Page 2

44	1165	polysilicon near2 insulator	USPAT;	2004/05/11
			US-PGPUB;	13:37
			EPO; JPO;	
			DERWENT;	·
			IBM TDB	
45	228	polysilicon adj insulator	USPAT;	2004/05/11
			US-PGPUB;	13:55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
46	23	(silicon adj germanium or sige) near10	USPAT;	2004/05/11
		promot\$5 near2 (crystal\$6 or crystalliz\$4	US-PGPUB;	14:01
		or recrystal\$5 or recrystalliz\$4)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
47	0	(silicon adj germanium or sige) near10	USPAT;	2004/05/11
		(si or silicon) near4 amporphous near20	US-PGPUB;	14:02
		(anneal\$4 or heat near2 treat\$4 or rapid	EPO; JPO;	-
		near2 thermal or laser)	DERWENT;	
			IBM_TDB	
48	58	(silicon adj germanium or sige) near10	USPAT;	2004/05/11
		(si or silicon) near4 amorphous near20	US-PGPUB;	15:31
		(anneal\$4 or heat near2 treat\$4 or rapid	EPO; JPO;	
		near2 thermal or laser)	DERWENT;	
	:		IBM_TDB	0004/05/11
49	274	(noguchi near2 shigeru).in.	USPAT;	2004/05/11
			US-PGPUB;	15:32
			EPO; JPO; DERWENT;	
			IBM TDB	
50	10	/w-washi maay2 ahigamu) in and /gigo or	USPAT;	2004/05/11
ا عن	10	(noguchi near2 shigeru).in. and (sige or silicon adj germanium)	US-PGPUB;	15:32
		SITICON adj germanium)	EPO; JPO;	15.52
i	İ		DERWENT;	
	ĺ		IBM TDB	
			TON TOD	

